July 2014

FDV303N
Digital FET, N-Channel

General Description

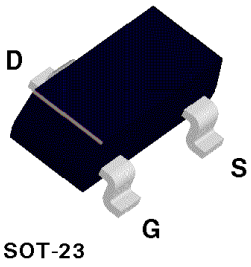
These N-Channel enhancement mode field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is tailored to minimize on-state resistance at low gate drive conditions. This device is designed especially for application in battery circuits using either one lithium or three cadmium or NMH cells. It can be used as an inverter or for high-efficiency miniature discrete DC/DC conversion in compact portable electronic devices like cellular phones and pagers. This device has excellent on-state resistance even at gate drive voltages as low as 2.5 volts.

Features

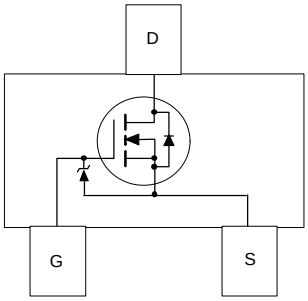
- 25 V, 0.68 A continuous, 2 A Peak.
  $R_{DS(ON)}$ = 0.45 Ω @ V_{GS} = 4.5 V
  $R_{DS(ON)}$ = 0.6 Ω @ V_{GS}= 2.7 V.
- Very low level gate drive requirements allowing direct operation in 3V circuits. $V_{GS(th)}$ < 1V.
- Gate-Source Zener for ESD ruggedness.>6kV Human Body Model
- Compact industry standard SOT-23 surface mount package.
- Alternative to TN0200T and TN0201T.

SOT-23	SuperSOT™-6	SuperSOT™-8	SO-8	SOT-223	SOIC-16

Mark:303



SOT-23



Absolute Maximum Ratings T_A = 25°C unless other wise noted

Symbol	Parameter	FDV303N	Units
V_{DSS}	Drain-Source Voltage, Power Supply Voltage	25	V
V_{GSS}	Gate-Source Voltage, V_{IN}	8	V
I_D	Drain/Output Current - Continuous	0.68	A
	- Pulsed	2	
P_D	Maximum Power Dissipation	0.35	W
T_J,T_{STG}	Operating and Storage Temperature Range	-55 to 150	°C
ESD	Electrostatic Discharge Rating MIL-STD-883D Human Body Model (100pf / 1500 Ohm)	6.0	kV
THERMAL CHARACTERISTICS			
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	357	°C/W

Electrical Characteristics (T_A = 25 °C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 µA	25			V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	I_D = 250 µA, Referenced to 25 °C		26		mV / °C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 20 V, V_{GS} = 0 V			1	µA
		T_J = 55°C			10	µA
I_{GSS}	Gate - Body Leakage Current	V_{GS} = 8 V, V_{DS} = 0 V			100	nA
ON CHARACTERISTICS (Note)						
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Temp. Coefficient	I_D = 250 µA, Referenced to 25 °C		-2.6		mV / °C
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 µA	0.65	0.8	1	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} = 4.5 V, I_D = 0.5 A		0.33	0.45	Ω
		T_J =125°C		0.52	0.8	
		V_{GS} = 2.7 V, I_D = 0.2 A		0.44	0.6	
$I_{D(ON)}$	On-State Drain Current	V_{GS} = 2.7 V, V_{DS} = 5 V	0.5			A
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 0.5 A		1.45		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 10 V, V_{GS} = 0 V, f = 1.0 MHz		50		pF
C_{oss}	Output Capacitance			28		pF
C_{rss}	Reverse Transfer Capacitance			9		pF
SWITCHING CHARACTERISTICS (Note)						
$t_{D(on)}$	Turn - On Delay Time	V_{DD} = 6 V, I_D = 0.5 A, V_{GS} = 4.5 V, R_{GEN} = 50 Ω		3	6	ns
t_r	Turn - On Rise Time			8.5	18	ns
$t_{D(off)}$	Turn - Off Delay Time			17	30	ns
t_f	Turn - Off Fall Time			13	25	ns
Q_g	Total Gate Charge	V_{DS} = 5 V, I_D = 0.5 A, V_{GS} = 4.5 V		1.64	2.3	nC
Q_{gs}	Gate-Source Charge			0.38		nC
Q_{gd}	Gate-Drain Charge			0.45		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I_S	Maximum Continuous Drain-Source Diode Forward Current				0.3	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 0.5 A (Note)		0.83	1.2	V

Note:

Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2.0%.

Typical Electrical Characteristics

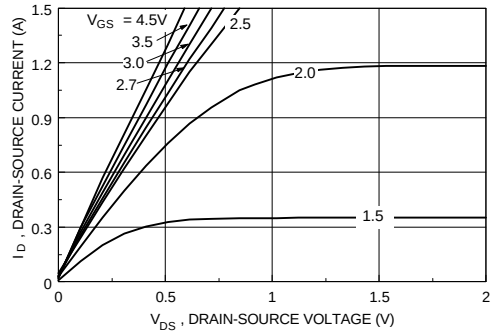


Figure 1. On-Region Characteristics.

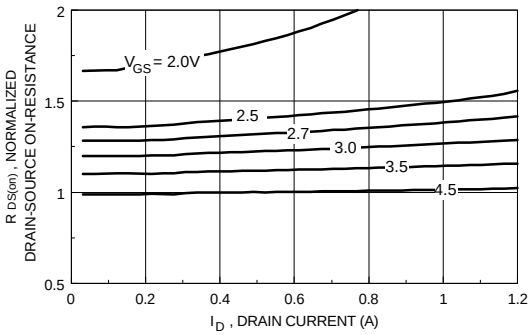


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

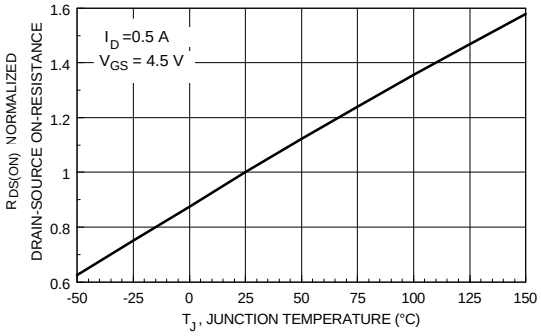


Figure 3. On-Resistance Variation with Temperature.

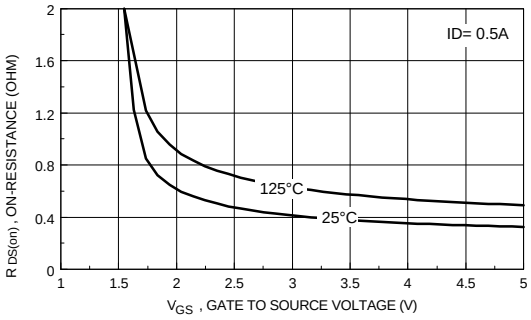


Figure 4. On Resistance Variation with Gate-To- Source Voltage.

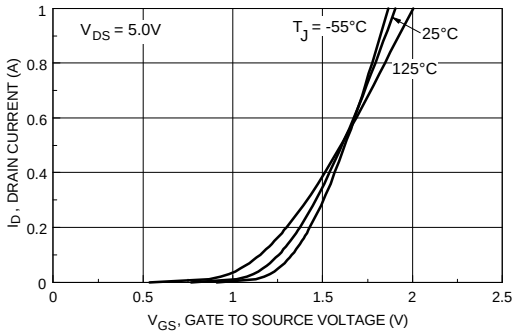


Figure 5. Transfer Characteristics.

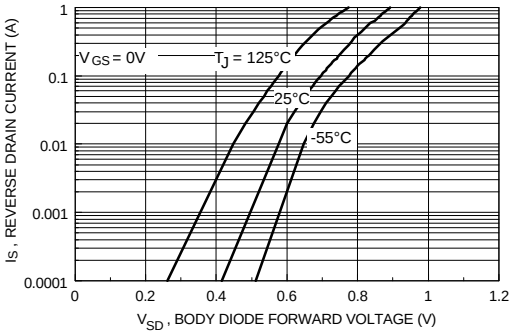


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Electrical And Thermal Characteristics

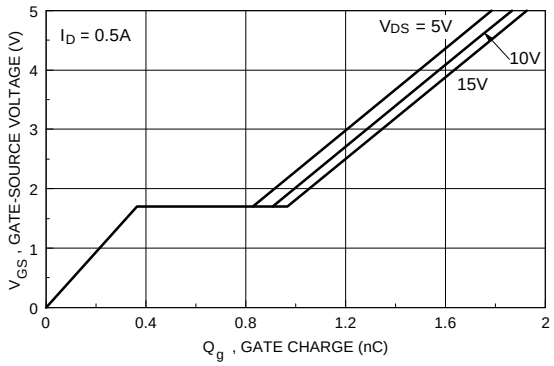


Figure 7. Gate Charge Characteristics.

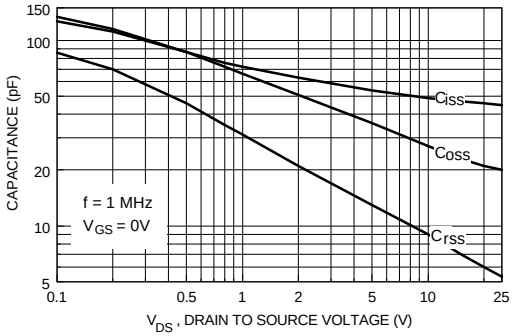


Figure 8. Capacitance Characteristics.

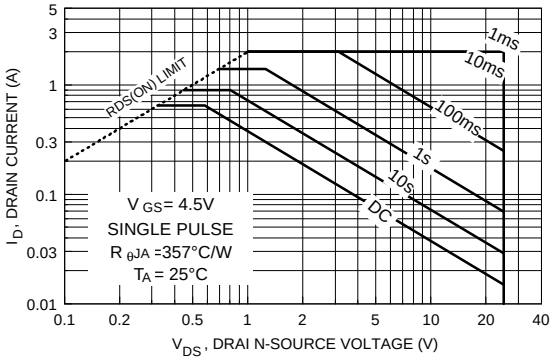


Figure 9. Maximum Safe Operating Area.

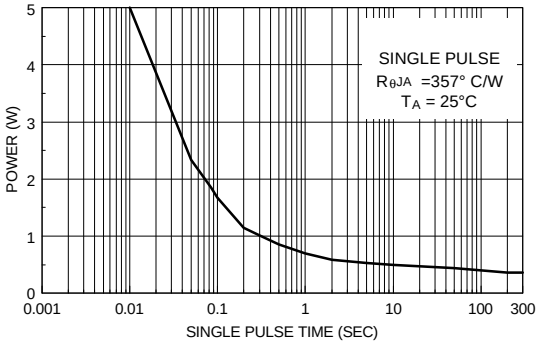


Figure 10. Single Pulse Maximum Power Dissipation.

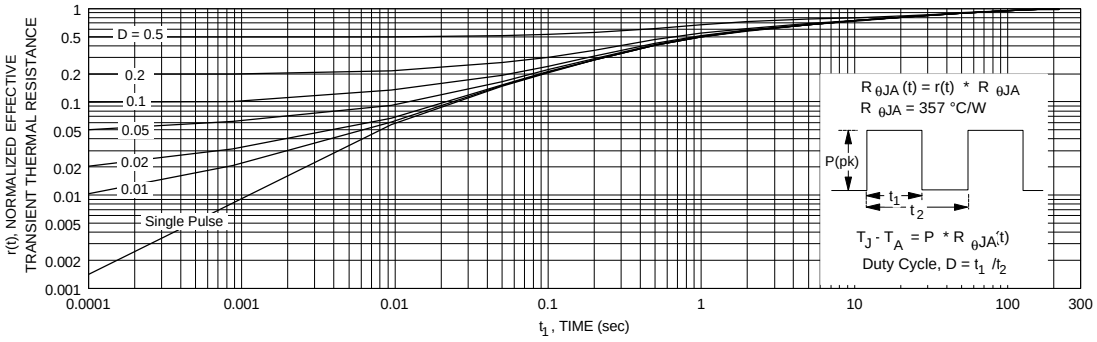
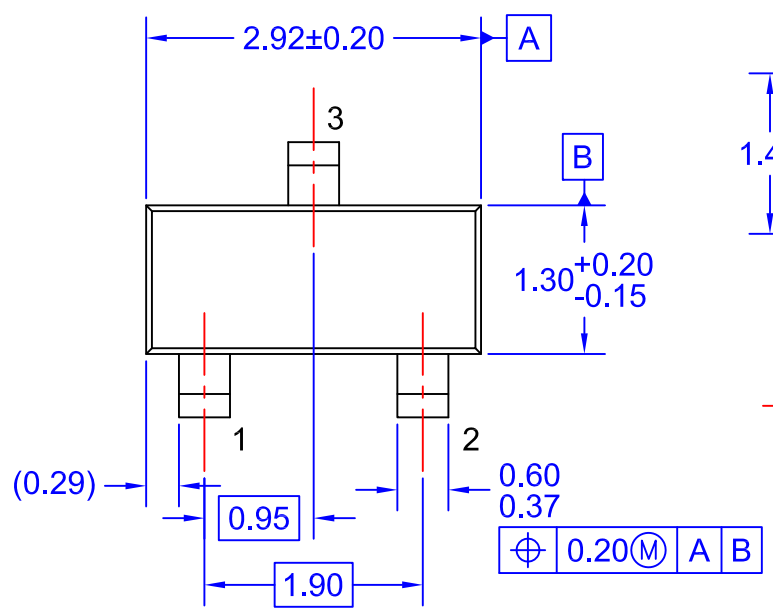
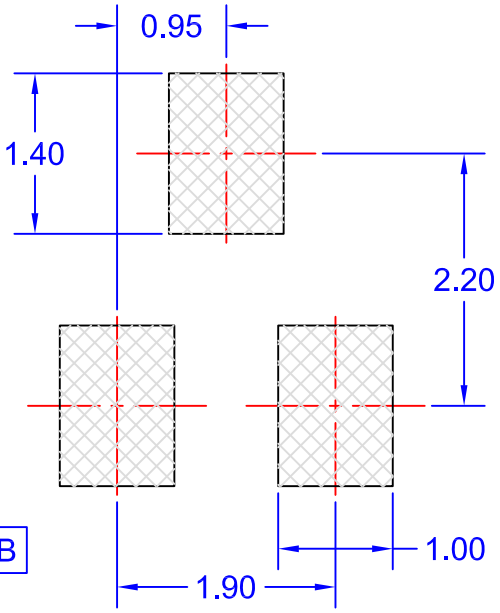
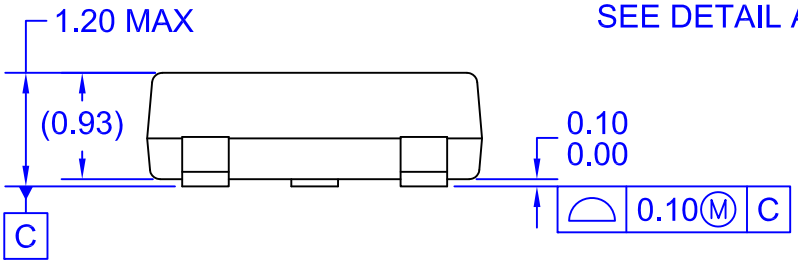


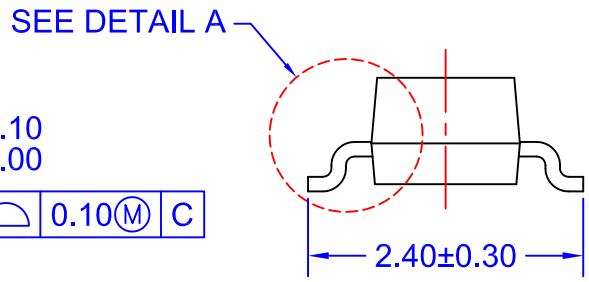
Figure 11. Transient Thermal Response Curve.

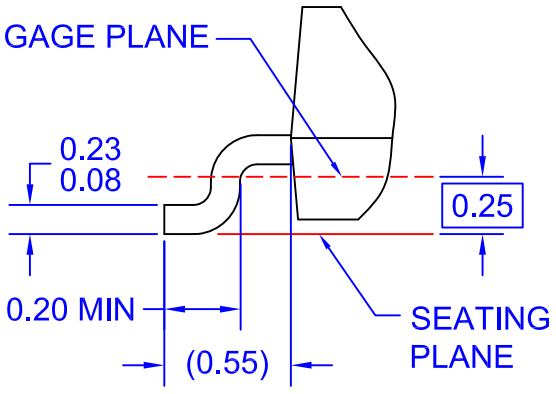




LAND PATTERN
RECOMMENDATION







DETAIL A
SCALE: 2X

NOTES: UNLESS OTHERWISE SPECIFIED

A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M - 2009.
E) DRAWING FILE NAME: MA03DREV12

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